10. A conductor which includes a substrate having a surface which defines an electrical flow path, at least part of which extends along at least part of the surface, wherein the said at least part of the surface is a doped part the electrical flow path extending laterally along and externally to said at least part of the surface.

11. A conductor as claimed in claim ~~10~~, in which the substrate has a passage extending through the substrate and the electrical flow path extends around the passage.

12. A circuit which includes a conductor as claimed in claim 11.

13. An electronic device which includes an electrical flow path, at least part of said flow path being formed by a body of a substrate material at least part of which is a doped part having a surface and implanted atoms at or below the surface, at least part of the surface defining a low resistance section of the electrical flow path at least part of which extends along at least part of the surface the electrical flow path extending laterally along and externally to said at least part of the surface.

14. A lateral electrical flow path, consisting of electron charges that are external to a surface of an n-type substrate material and which, in contrast to external electron-orbitals on a surface, are free to move under the influence of an electric-field applied along the surface of the substrate material, the charges being generated by a high density of donor-flaws within the substrate, at and near to the surface of the substrate.

15. An electrical flow path at least part of which is formed by a body of a substrate material at least part of which is a doped part having a surface and implanted atoms at or below the surface, at least part of the surface defining a low resistance section of the electrical flow path at least part of which extends along at least part of the surface, in which the substrate material has a low electron-affinity and is selected from diamond, graphene, graphene-dominated materials, polymers, cubic boron nitride, aluminium-nitride, gallium-nitride and β-alumina and lateral conduction occurring externally to the surface of the substrate material.

~~8~~ 7. An electrical flow path as claimed in any one of claims 1 to ~~7~~ 6 inclusive, in which the implanted atoms are selected from oxygen, hydrogen, lithium, nitrogen, fluorine, chlorine, sulphur, phosphorus, arsenic and combinations thereof.

~~9~~ 8. An electrical flow path as claimed in any one of claims 1 to ~~8~~ 7 inclusive, in which at least some of the implanted atoms are at depths of between about 0.1 Å and 5000 Å below the surface of the substrate.

~~10~~ 9. An electrical flow path as claimed in any one of claims 1 to ~~9~~ 8 inclusive, in which the density of the implanted atoms is between about 10^{17} cm $^{-3}$ and 10^{23} cm^{-3}.

~~11~~ 10. A conductor which includes a substrate having a surface which defines an electrical flow path, at least part of which extends along at least part of the surface, wherein the said at least part of the surface is a doped part the electrical flow path extending laterally along and externally to said at least part of the surface.

~~12~~ 11. A conductor as claimed in claim ~~11~~ 10, in which the substrate has a passage extending through the substrate and the electrical flow path extends around the passage.

~~13~~ 12. A circuit which includes a conductor as claimed in claim 11.

~~14~~ 13. An electronic device which includes an electrical flow path, at least part of said flow path being formed by a body of a substrate material at least part of which is a doped part having a surface and implanted atoms at or below the surface, at least part of the surface defining a low resistance section of the electrical flow path at least part of which extends along at least part of the surface the electrical flow path extending laterally along and externally to said at least part of the surface.

~~15~~ 14. A lateral electrical flow path, consisting of electron charges that are external to a surface of an n-type substrate-material and which, in contrast to external electron-orbitals on a surface, are free to move under the influence of an electric-field applied along the surface of the substrate material, the charges being generated by a high density of donor-flaws within the substrate, at and near to the surface of the substrate.

10. A conductor which includes a substrate having a surface which defines an electrical flow path, at least part of which extends along at least part of the surface, wherein the said at least part of the surface is a doped part the electrical flow path extending laterally along and externally to said at least part of the surface.

11. A conductor as claimed in claim 10, in which the substrate has a passage extending through the substrate and the electrical flow path extends around the passage.

12. A circuit which includes a conductor as claimed in claim 11.

13. An electronic device which includes an electrical flow path, at least part of said flow path being formed by a body of a substrate material at least part of which is a doped part having a surface and implanted atoms at or below the surface, at least part of the surface defining a low resistance section of the electrical flow path at least part of which extends along at least part of the surface the electrical flow path extending laterally along and externally to said at least part of the surface.

14. A lateral electrical flow path, consisting of electron charges that are external to a surface of an n-type substrate-material and which, in contrast to external electron-orbitals on a surface, are free to move under the influence of an electric-field applied along the surface of the substrate material, the charges being generated by a high density of donor-flaws within the substrate, at and near to the surface of the substrate.

15. An electrical flow path at least part of which is formed by a body of a substrate material at least part of which is a doped part having a surface and implanted atoms at or below the surface, at least part of the surface defining a low resistance section of the electrical flow path at least part of which extends along at least part of the surface, in which the substrate material has a low electron-affinity and is selected from diamond, graphene, graphene-dominated materials, polymers, cubic boron nitride, aluminium-nitride, gallium-nitride and β-alumina and lateral conduction occurring externally to the surface of the substrate material.